

NTE291 (NPN) & NTE292 (PNP) Silicon Complementary Transistors Medium Power Amp, Switch

Description:

The NTE291 (NPN) and NTE292 (PNP) are General–Purpose Medium–Power silicon complementary transistors in a TO220 type package designed for switching and amplifier applications. They are especially designed for series and shunt regulators and as a driver and output stage of high–fidelity amplifiers.

Features:

Low Saturation Voltage

Absolute Maximum Ratings:
Collector-to-Base Voltage, V _{CBO}
Collector–to–Emitter Voltage ($R_{BB} = 100\Omega$, $V_{BB} = 0$), V_{CEX}
Collector-to-Emitter Voltage, V _{CEO}
Emitter–To–Base Voltage, V _{EBO}
Continuous Collector Current ($T_C \le +106^{\circ}C$), I_C
Continuous Base Current ($T_C \le +130^{\circ}C$), $I_B \dots 2A$
Power Dissipation, P _D
$T_C = +100^{\circ}C$
Derate Linearly Above T _C = +100°C
$T_C = +25^{\circ}C$
Derate Linearly Above T _C = +25°C
$T_A = +25^{\circ}C$
$T_A = +25^{\circ}C$
Operating Temperature Range, T _{opr} –65° to +150°C
Storage Temperature Range, T _{stq} –65° to +150°C
Lead Temperature (During Soldering), T _I
At distance ≥ 1/8 in. (3.17mm) from case for 10s Max+235°C
Thermal Resistance, Junction-to-Case, R _{thJC}
Thermal Resistance, Junction–to–Ambient, R _{thJA}

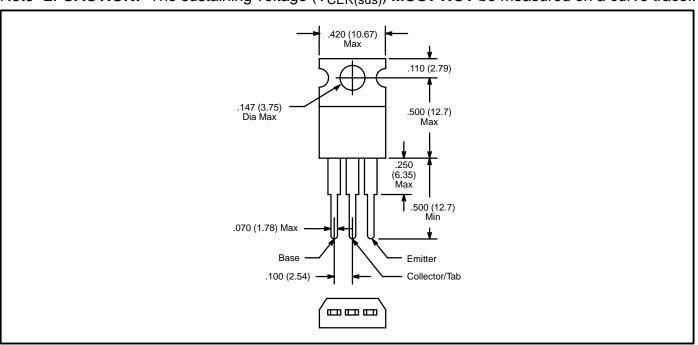
Note 1. NTE292MCP is a matched complementary pair containing 1 each of NTE291 (NPN) and NTE292 (PNP).

Electrical Characteristics: $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CEO}	$V_{CE} = 60V, I_B = 0$	_	_	1	mA
Collector Cutoff Current	I _{CER}	$R_{BE} = 100\Omega, V_{CE} = 120V$	_	_	0.1	mA
		$R_{BE} = 100\Omega, V_{CE} = 120V,$ $T_{C} = +100^{\circ}C$	_	_	2	mA
Collector Cutoff Current	I _{CEX}	$V_{CE} = 120V, V_{BE} = -1.5V$	_	_	0.1	mA
		$V_{CE} = 120V, V_{BE} = -1.5V,$ $T_{C} = +100^{\circ}C$	_	_	2	mA
Emitter Cutoff Current	I _{EBO}	$V_{BE} = -5V, I_C = 0$	_	_	1	mA
Collector–to–Emitter Sustaining Voltage	V _{CEO(sus)}	$I_C = 0.1A$, $I_B = 0$, Note 1	120	_	_	V
Collector–to–Emitter Sustaining Voltage	V _{CER(sus)}	$R_{BE} = 100\Omega$, $I_C = 0.1A$, Note 2	130	_	_	V
DC Forward Current	h _{FE}	V _{CE} = 4V, I _C = 1.5A, Note 1	15	_	150	
		V _{CE} = 2.5V, I _C = 4A, Note 1	2	_	_	
Base-to-Emitter Voltage	V _{BE}	$V_{CE} = 4V, I_{C} = 1.5A, Note 1$	_	_	2	V
		$V_{CE} = 2.5V, I_{C} = 4A, Note 1$	_	_	3.5	V
Collector–to–Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 1.5A$, $I_B = 0.15A$, Note 1	_	_	1.2	V
		I _C = 4A, I _B = 2A, Note 1	_	_	2.5	V
Small Signal Forward Current Transfer Ratio	h _{fe}	$V_{CE} = 4V, I_{C} = 0.5A, f = 50kHz$	20	_	_	
Gain Bandwidth Product	f _T	$V_{CE} = 4V, I_{C} = 0.5A$	4	_	_	MHz
Small Signal Forward Current Transfer Ratio	h _{fe}	$V_{CE} = 4V, I_{C} = 0.5A, f = 50kHz$	4	_	_	
Collector-to-Base Capacitance	C _{obo}	$V_{CB} = 10V, I_{C} = 0, f = 1MHz$			250	pF

Note 1. Pulsed: Pulse Duration = $300\mu s$, Duty Factor = 0.018.

Note 2. **CAUTION:** The sustaining voltage $(V_{CER(sus)})$ **MUST NOT** be measured on a curve tracer.



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